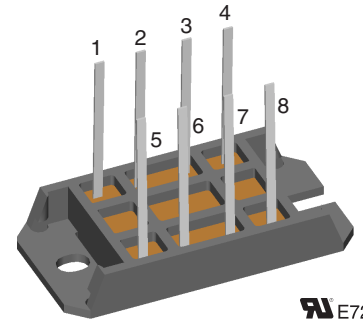
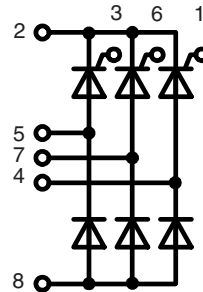


Three Phase Half Controlled Rectifier Bridge

$I_{dAVM} = 43 \text{ A}$
 $V_{RRM} = 1200\text{-}1600 \text{ V}$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1300	1200	VVZ 40-12io1
1500	1400	VVZ 40-14io1
1700	1600	VVZ 40-16io1



Symbol	Conditions	Maximum Ratings	Features
I_{dAV}	$T_K = 100^\circ\text{C}$; module	34 A	<ul style="list-style-type: none"> • Package with DCB ceramic base plate • Isolation voltage 3600 V~ • Planar passivated chips • Soldering terminals • UL registered E 72873
I_{dAVM}	module	43 A	
I_{FRMS}, I_{TRMS}	per leg	25 A	
I_{FSM}, I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	320 A 340 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	290 A 310 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	510 A ² s 485 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	420 A ² s 400 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$ non repetitive, $I_T = 1/3 \cdot I_{dAV}$	150 A/ μs 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000 V/ μs
V_{RGM}			10 V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$	$\leq 10 \text{ W}$
		$t_p = 500 \mu\text{s}$	$\leq 5 \text{ W}$
		$t_p = 10 \text{ ms}$	$\leq 1 \text{ W}$
P_{GAVM}			0.5 W
T_{VJ}			-40...+125 °C
T_{VJM}			125 °C
T_{stg}			-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	3000 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3600 V~
M_d	Mounting torque	(M5)	2-2.5 Nm
		(10-32 UNF)	18-22 lb.in.
Weight	typ.		28 g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

